

IN THE CLAIMS

Please cancel claims 4-10, 14-22, and 25-28 without prejudice or disclaimer of their subject matter, and add new claims 29-35, as follows:

Claims 1 -28. (Canceled)

1 29. (New) A flat panel display, comprising a plurality of sub-pixels driven by thin
2 film transistors, each of the thin film transistors including a source electrode, a drain electrode,
3 a gate electrode, and a polysilicon semiconductor layer and each of the sub-pixels including a
4 first electrode, a second electrode, and an emitting layer disposed between the first electrode
5 and the second electrode, wherein one of the source electrode and the drain electrode includes:
6 a first titanium layer contacting the semiconductor layer;
7 an aluminum-based metal layer arranged on the first titanium layer;
8 a second titanium layer arranged on the aluminum-based metal layer and
9 contacting the first electrode;
10 a first titanium nitride layer disposed between the first titanium layer and the
11 aluminum-based metal layer, the first titanium nitride layer preventing titanium from the first
12 titanium layer and aluminum from the aluminum-based metal layer reacting with each other; and
13 a second titanium nitride layer disposed between the second titanium layer and
14 the aluminum-based metal layer, the second titanium nitride layer preventing titanium from the
15 second titanium layer and aluminum from the aluminum-based metal layer reacting with each

other;

wherein the titanium nitride layer contains 5 to 85wt% of nitrogen.

30. (New) The flat panel display of claim 29, wherein the titanium nitride layer has a thickness of about 100 to 600Å.

31. (New) The flat panel display of claim 29, wherein the first titanium nitride layer has a thickness of about 100 to 400Å.

32. (New) The flat panel display of claim 29, wherein the second titanium nitride layer has a thickness of about 200 to 600Å.

33. (New) The flat panel display of claim 29, wherein the titanium nitride layers have a thickness of about 300Å.

34. (New) A flat panel display, comprising a plurality of sub-pixels driven by thin film transistors, each of the thin film transistors including a source electrode, a drain electrode, a gate electrode, and a polysilicon semiconductor layer each of the sub-pixels including a first electrode, a second electrode, and an emitting layer disposed between the first electrode and the second electrode, wherein one of the source electrode and the drain electrode includes:

a first titanium layer contacting the semiconductor layer;

7 an aluminum-based metal layer arranged on the first titanium layer;
8 a second titanium layer arranged on the aluminum-based metal layer and
9 contacting the first electrode;
10 a first titanium nitride layer disposed between the first titanium layer and the
11 aluminum-based metal layer, the first titanium nitride layer preventing titanium from the first
12 titanium layer and aluminum from the aluminum-based metal layer reacting with each other; and
13 a second titanium nitride layer disposed between the second titanium layer and
14 the aluminum-based metal layer, the second titanium nitride layer preventing titanium from the
15 second titanium layer and aluminum from the aluminum-based metal layer reacting with each
16 other;
17 wherein the aluminum-based metal layer is an aluminum alloy containing about
18 0.5 to 5 wt% of one element being selected from the group consisting of silicon, copper,
19 neodymium, platinum, and nickel.

1 35. (New) The flat panel display of claim 34, wherein the aluminum-based metal
2 layer is an aluminum-silicon alloy containing about 2 wt% of silicon.